

# 74AHC374; 74AHCT374

Octal D-type flip-flop; positive edge-trigger; 3-state

Rev. 03 — 12 June 2008

Product data sheet

## 1. General description

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The 74AHC374; 74AHCT374 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC374; 74AHCT374 comprises eight D-type flip-flops featuring separate D-type inputs for each flip-flop and 3-state outputs for bus oriented applications. A clock input (CP) and an output enable input ( $\overline{OE}$ ) are common to all flip-flops.

The eight flip-flops will store the state of their individual D inputs that meet the set-up and hold times requirements for the LOW-to-HIGH CP transition.

When  $\overline{OE}$  is LOW the content of the eight flip-flops is available at the outputs. When  $\overline{OE}$  is HIGH, the outputs go to the high-impedance OFF-state. Operation of the  $\overline{OE}$  input does not affect the state of the flip-flops.

## 2. Features

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- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than  $V_{CC}$
- Common 3-state output enable input
- Input levels:
  - ◆ For 74AHC374: CMOS level
  - ◆ For 74AHCT374: TTL level
- ESD protection:
  - ◆ HBM EIA/JESD22-A114E exceeds 2000 V
  - ◆ MM EIA/JESD22-A115-A exceeds 200 V
  - ◆ CDM EIA/JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

### 3. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
<b>74AHC374</b>				
74AHC374D	-40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC374PW	-40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
<b>74AHCT374</b>				
74AHCT374D	-40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHCT374PW	-40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1

### 4. Functional diagram

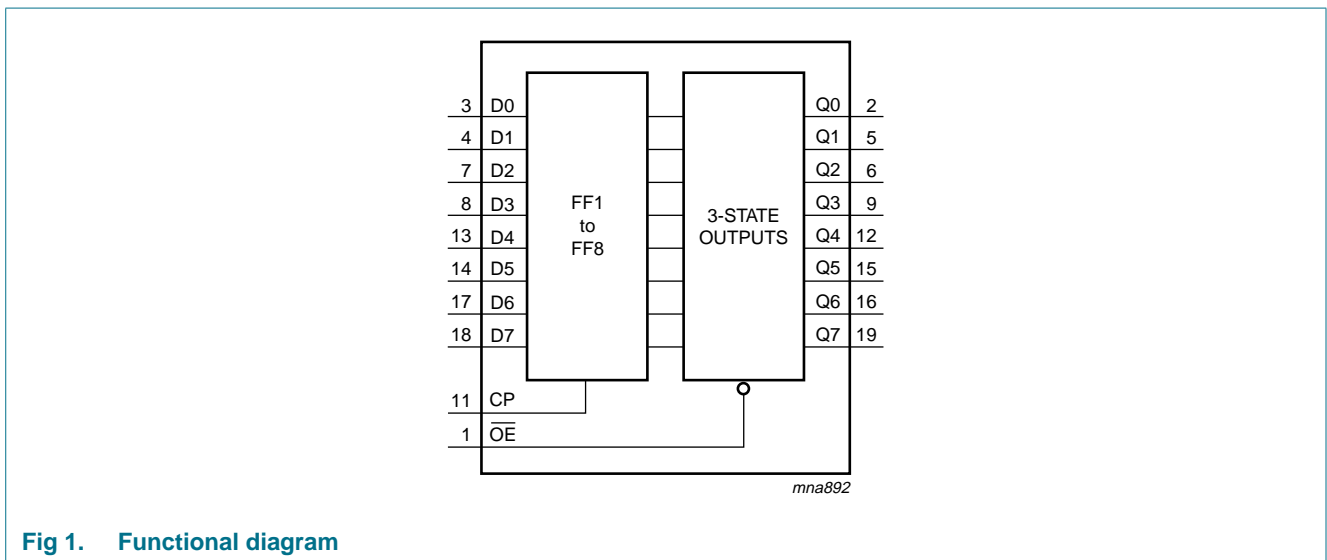


Fig 1. Functional diagram

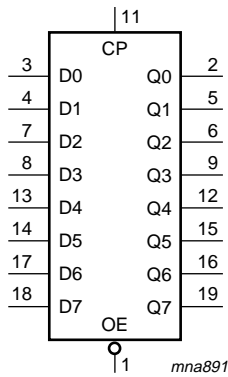


Fig 2. Logic symbol

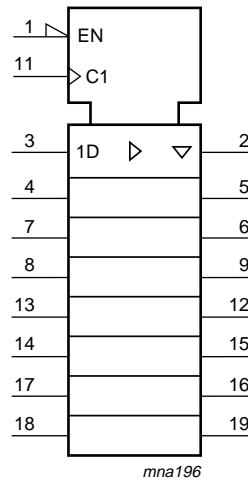


Fig 3. IEC logic symbol

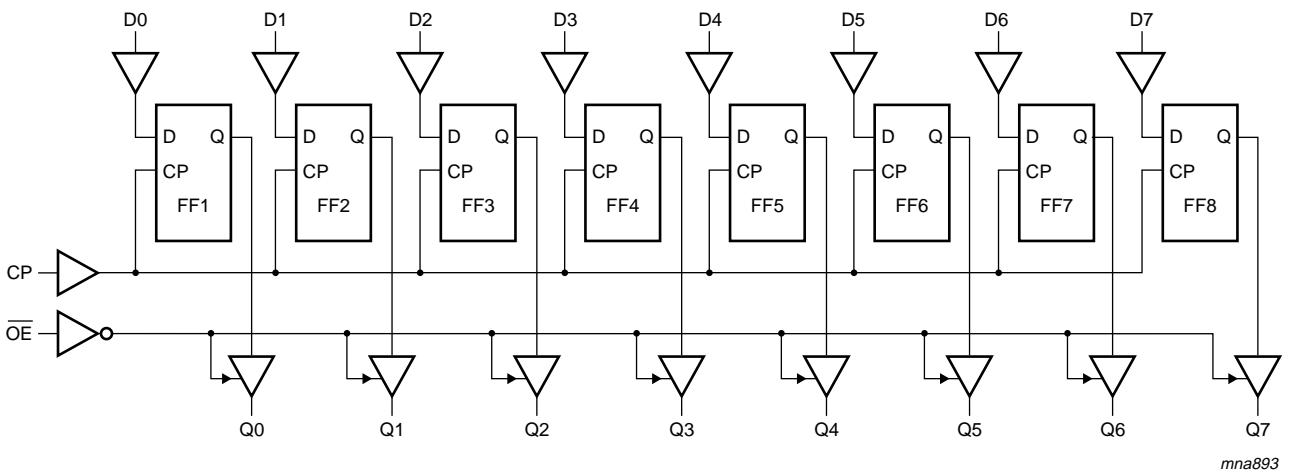


Fig 4. Logic diagram

## 5. Pinning information

### 5.1 Pinning

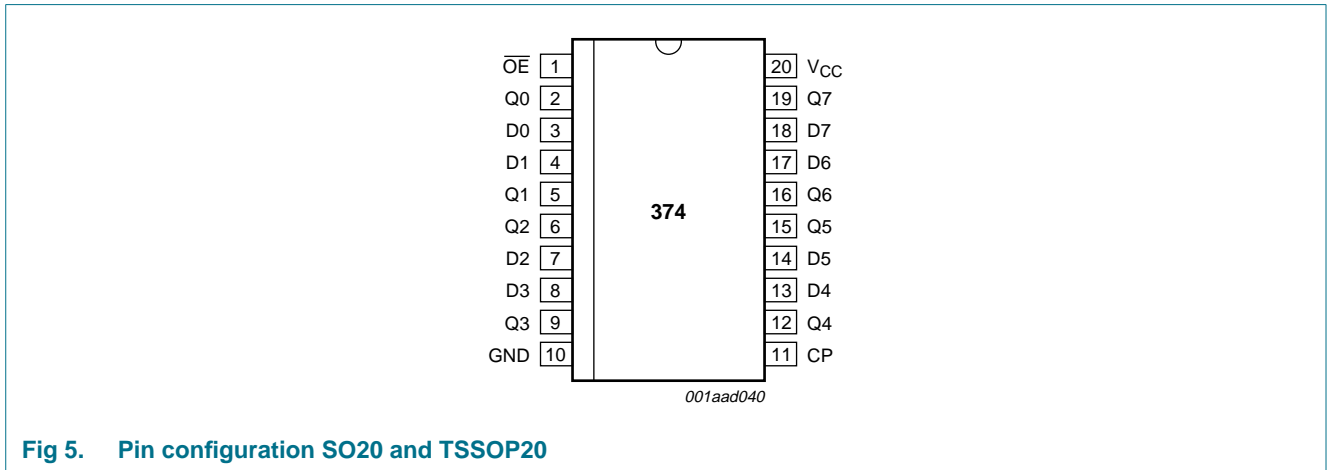


Fig 5. Pin configuration SO20 and TSSOP20

### 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE	1	3-state output enable input (active LOW)
Q0	2	3-state flip-flop output
D0	3	data input
D1	4	data input
Q1	5	3-state flip-flop output
Q2	6	3-state flip-flop output
D2	7	data input
D3	8	data input
Q3	9	3-state flip-flop output
GND	10	ground (0 V)
CP	11	clock input (LOW-to-HIGH, edge triggered)
Q4	12	3-state flip-flop output
D4	13	data input
D5	14	data input
Q5	15	3-state flip-flop output
Q6	16	3-state flip-flop output
D6	17	data input
D7	18	data input
Q7	19	3-state flip-flop output
V <sub>CC</sub>	20	supply voltage

## 6. Functional description

Table 3. Function table<sup>[1]</sup>

Operating mode	Control		Input	Internal flip-flop	Output
	$\overline{OE}$	CP	Dn		Q0 to Q7
Load and read register	L	↑	l	L	L
	L	↑	h	H	H
Load register and disable outputs	H	↑	l	L	Z
	H	↑	h	H	Z

- [1] H = HIGH voltage level;  
 h = HIGH voltage level one setup time prior to the LOW-to-HIGH CP transition;  
 L = LOW voltage level;  
 l = LOW voltage level one setup time prior to the LOW-to-HIGH CP transition;  
 X = don't care;  
 ↑ = LOW-to-HIGH CP transition;  
 Z = high-impedance OFF-state.

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$V_I$	input voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5$ V	<sup>[1]</sup> -20	-	mA
$I_{OK}$	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	<sup>[1]</sup> -20	+20	mA
$I_O$	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5)$ V	-25	+25	mA
$I_{CC}$	supply current		-	+75	mA
$I_{GND}$	ground current		-75	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	<sup>[2]</sup> -	500	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.  
 [2] For SO20 packages: above 70 °C the value of  $P_{tot}$  derates linearly at 8 mW/K.  
 For TSSOP20 packages: above 60 °C the value of  $P_{tot}$  derates linearly at 5.5 mW/K.

**8. Recommended operating conditions**

**Table 5. Operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>74AHC374</b>						
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	100	ns/V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	20	ns/V
<b>74AHCT374</b>						
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	20	ns/V

**9. Static characteristics**

**Table 6. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74AHC374</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I <sub>O</sub> = -50 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
	I <sub>O</sub> = -8.0 mA; V <sub>CC</sub> = 4.5 V	3.94	-	-	3.80	-	3.70	-	V	
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 50 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
	I <sub>O</sub> = 8.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.36	-	0.44	-	0.55	V	

**Table 6. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$I_I$	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 0\text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	$\pm 0.25$	-	$\pm 2.5$	-	$\pm 10.0$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 5.5\text{ V}$	-	-	4.0	-	40	-	80	$\mu\text{A}$
$C_I$	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
$C_O$	output capacitance		-	4	-	-	-	-	-	pF

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$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5\text{ V}$ to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5\text{ V}$ $I_O = -50\ \mu\text{A}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -8.0\text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5\text{ V}$ $I_O = 50\ \mu\text{A}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 8.0\text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
$I_I$	input leakage current	$V_I = 5.5\text{ V}$ or GND; $V_{CC} = 0\text{ V}$ to 5.5 V	-	-	0.1	-	1.0	-	2.0	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 5.5\text{ V}$	-	-	$\pm 0.25$	-	$\pm 2.5$	-	$\pm 10.0$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 5.5\text{ V}$	-	-	4.0	-	40	-	80	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input pin; $V_I = V_{CC} - 2.1\text{ V}$ ; other pins at $V_{CC}$ or GND; $I_O = 0\text{ A}$ ; $V_{CC} = 4.5\text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
$C_I$	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF
$C_O$	output capacitance		-	4	-	-	-	-	-	pF

## 10. Dynamic characteristics

**Table 7. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
<b>74AHC374</b>										
t <sub>pd</sub>	propagation delay	CP to Qn; see <a href="#">Figure 6</a> and <a href="#">Figure 8</a> <sup>[2]</sup>								
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	6.4	12.7	1.0	15.0	1.0	16.0	ns
		C <sub>L</sub> = 50 pF	-	8.4	16.2	1.0	18.5	1.0	20.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	4.4	8.1	1.0	9.5	1.0	10.0	ns
t <sub>en</sub>	enable time	OE to Qn; see <a href="#">Figure 7</a> <sup>[3]</sup>								
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	5.5	11.0	1.0	13.0	1.0	14.0	ns
		C <sub>L</sub> = 50 pF	-	7.3	14.5	1.0	16.5	1.0	18.0	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.9	7.6	1.0	9.0	1.0	9.5	ns
t <sub>dis</sub>	disable time	OE to Qn; see <a href="#">Figure 7</a> <sup>[4]</sup>								
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	5.6	10.5	1.0	12.5	1.0	13.0	ns
		C <sub>L</sub> = 50 pF	-	9.4	14.0	1.0	16.0	1.0	17.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	4.2	6.8	1.0	8.0	1.0	8.5	ns
f <sub>max</sub>	maximum frequency	see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	80	130	-	70	-	70	-	MHz
		C <sub>L</sub> = 50 pF	55	85	-	50	-	50	-	MHz
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	130	185	-	110	-	110	-	MHz
t <sub>w</sub>	pulse width	CP HIGH or LOW; see <a href="#">Figure 6</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	5.0	-	-	5.5	-	5.5	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	5.0	-	-	5.0	-	5.0	-	ns
t <sub>su</sub>	set-up time	Dn to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	4.5	-	-	4.0	-	4.0	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	3.0	-	-	3.0	-	3.0	-	ns



**Table 7. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	Min	Max	
t <sub>h</sub>	hold time	Dn to CP; see <a href="#">Figure 8</a>								
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	2.0	-	2.0	-	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[5]</sup>	-	10	-	-	-	-	-	pF
<b>74AHCT374; V<sub>CC</sub> = 4.5 V to 5.5 V</b>										
t <sub>pd</sub>	propagation delay	CP to Qn; see <a href="#">Figure 6</a> and <a href="#">Figure 8</a> <sup>[2]</sup>								
		C <sub>L</sub> = 15 pF	-	4.3	9.4	1.0	10.5	1.0	12.0	ns
		C <sub>L</sub> = 50 pF	-	5.6	10.4	1.0	11.5	1.0	13.0	ns
t <sub>en</sub>	enable time	OE to Qn; see <a href="#">Figure 7</a> <sup>[3]</sup>								
		C <sub>L</sub> = 15 pF	-	3.5	10.2	1.0	11.5	1.0	13.0	ns
		C <sub>L</sub> = 50 pF	-	4.8	11.2	1.0	12.5	1.0	14.0	ns
t <sub>dis</sub>	disable time	OE to Qn; see <a href="#">Figure 7</a> <sup>[4]</sup>								
		C <sub>L</sub> = 15 pF	-	3.6	10.2	1.0	11.0	1.0	13.0	ns
		C <sub>L</sub> = 50 pF	-	5.7	11.2	1.0	12.0	1.0	14.0	ns
f <sub>max</sub>	maximum frequency	see <a href="#">Figure 6</a>								
		C <sub>L</sub> = 15 pF	90	140	-	80	-	80	-	MHz
		C <sub>L</sub> = 50 pF	85	130	-	75	-	75	-	MHz
t <sub>W</sub>	pulse width	CP HIGH or LOW; see <a href="#">Figure 6</a>	6.5	-	-	6.5	-	6.5	-	ns
t <sub>su</sub>	set-up time	Dn to CP; see <a href="#">Figure 8</a>	2.5	-	-	2.5	-	2.5	-	ns
t <sub>h</sub>	hold time	Dn to CP; see <a href="#">Figure 8</a>	2.5	-	-	2.5	-	2.5	-	ns
C <sub>PD</sub>	power dissipation capacitance	f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub> <sup>[5]</sup>	-	12	-	-	-	-	-	pF

[1] Typical values are measured at nominal supply voltage (V<sub>CC</sub> = 3.3 V and V<sub>CC</sub> = 5.0 V).

[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[3] t<sub>en</sub> is the same as t<sub>PZH</sub> and t<sub>PZL</sub>.

[4] t<sub>dis</sub> is the same as t<sub>PHZ</sub> and t<sub>PLZ</sub>.

[5] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

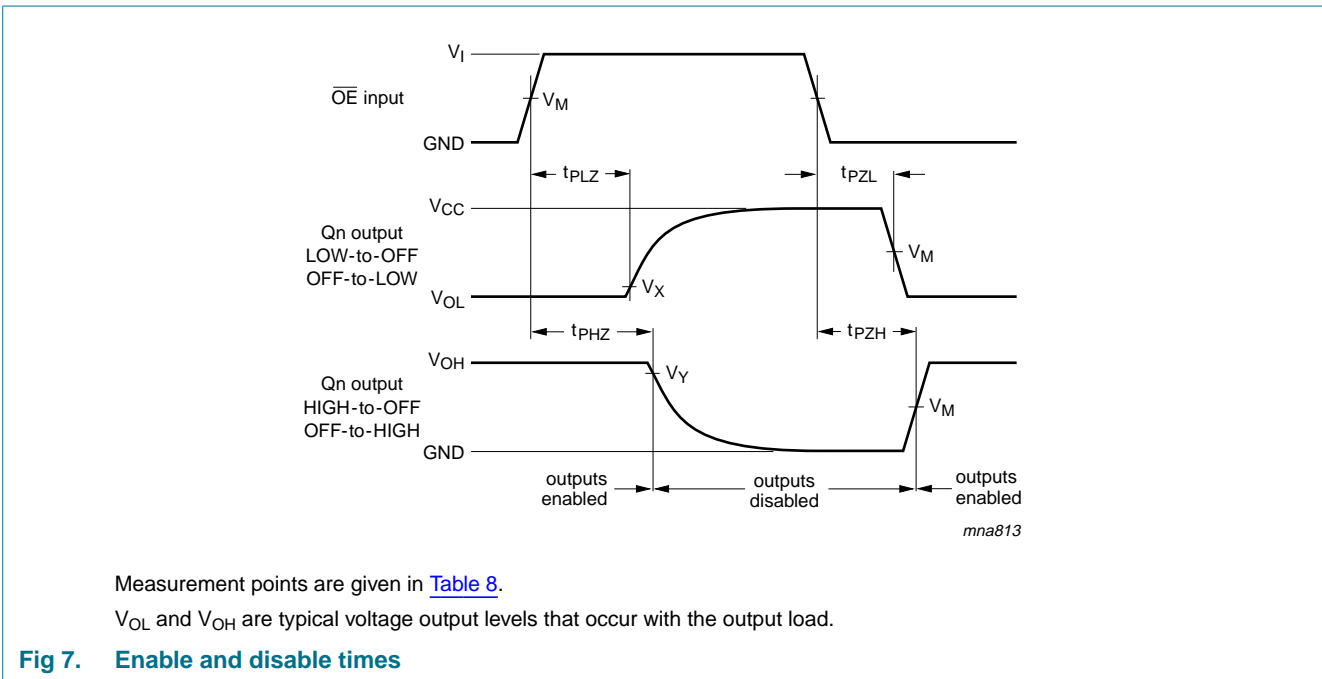
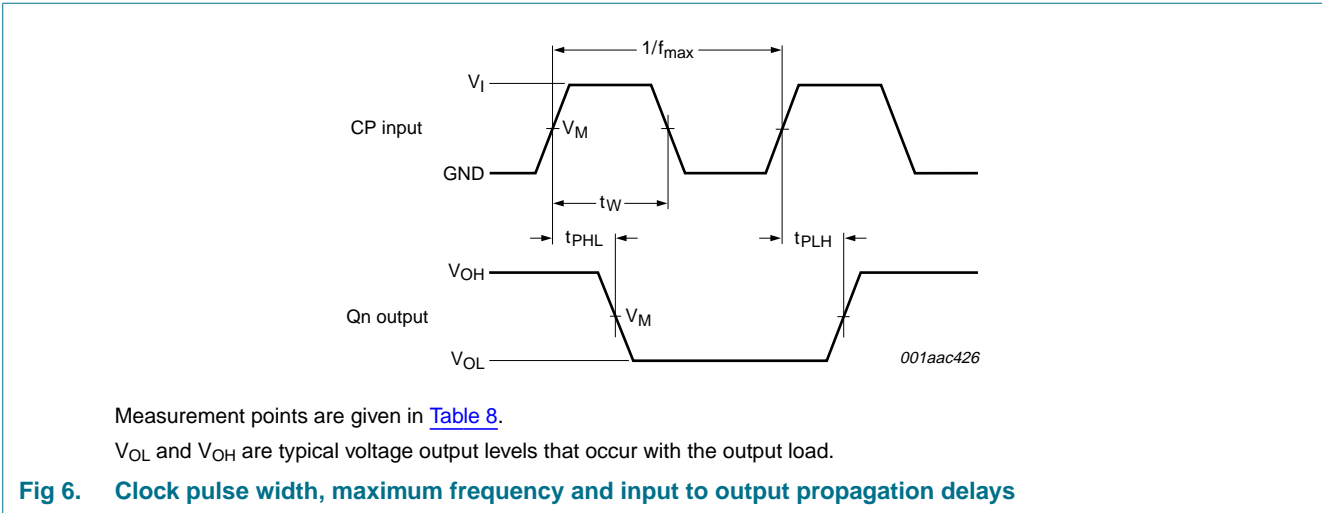
C<sub>L</sub> = output load capacitance in pF;

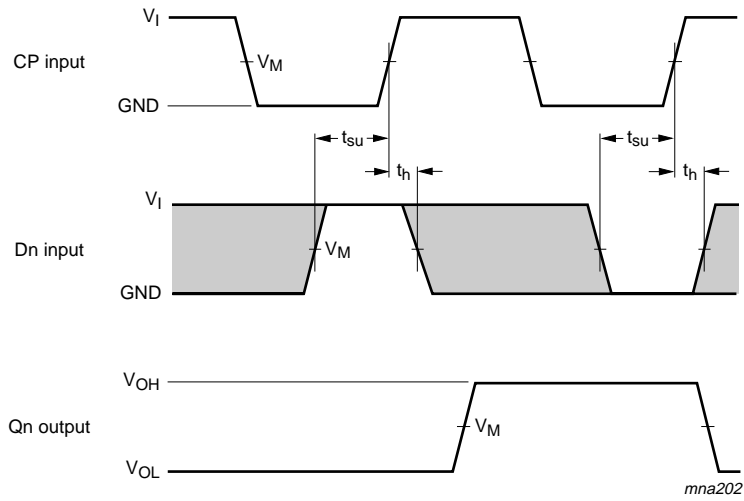
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

## 10.1 Waveforms



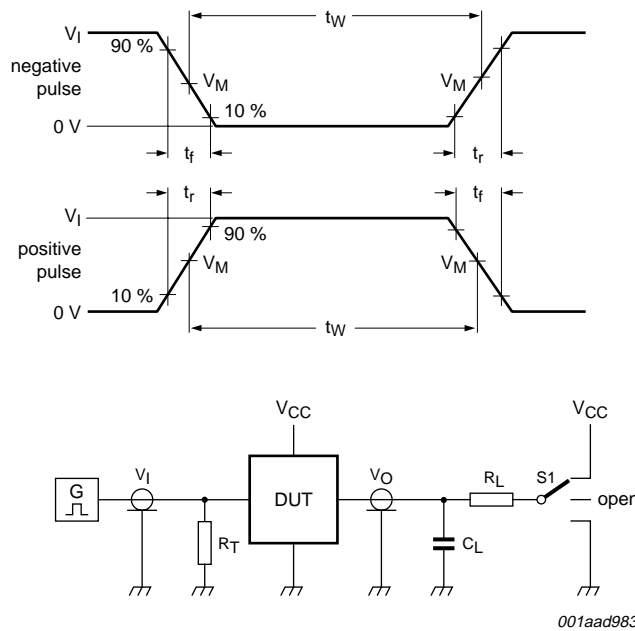


Measurement points are given in [Table 8](#).  
 The shaded areas indicate when the input is permitted to change for predictable output performance.  
 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

**Fig 8. Data set-up and hold times**

**Table 8. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
74AHC374	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$
74AHCT374	1.5 V	$0.5 \times V_{CC}$	$V_{OL} + 0.3 V$	$V_{OH} - 0.3 V$



Test data is given in [Table 9](#).

Definitions test circuit:

$R_T$  = termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = load capacitance including jig and probe capacitance.

$R_L$  = load resistance.

S1 = test selection switch.

**Fig 9. Test circuitry for measuring switching times**

**Table 9. Test data**

Type	Input		Load		S1 position		
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74AHC374	$V_{CC}$	$\leq 3.0$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$
74AHCT374	3.0 V	$\leq 3.0$ ns	15 pF, 50 pF	1 k $\Omega$	open	GND	$V_{CC}$

## 11. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

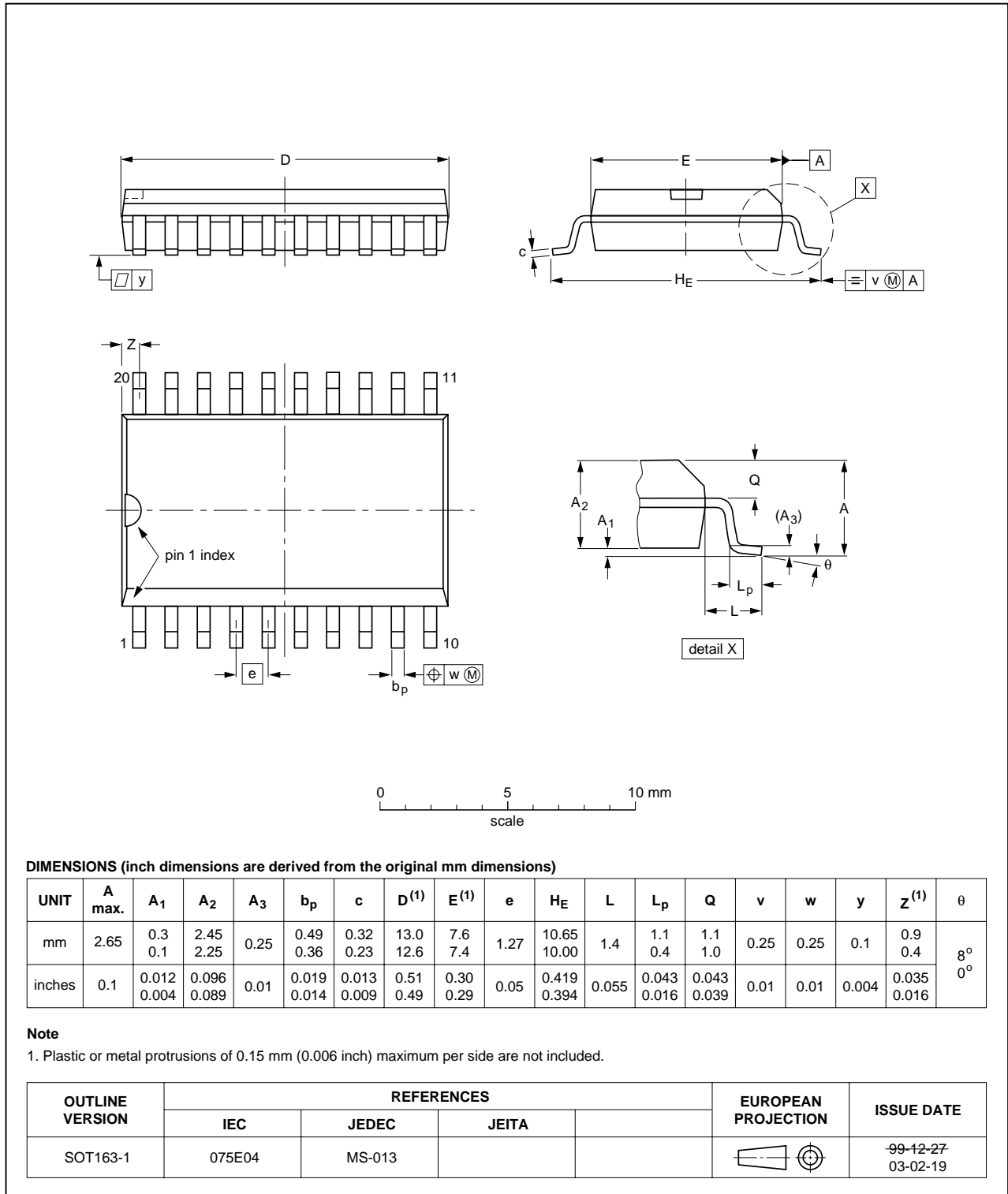


Fig 10. Package outline SOT163-1 (SO20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

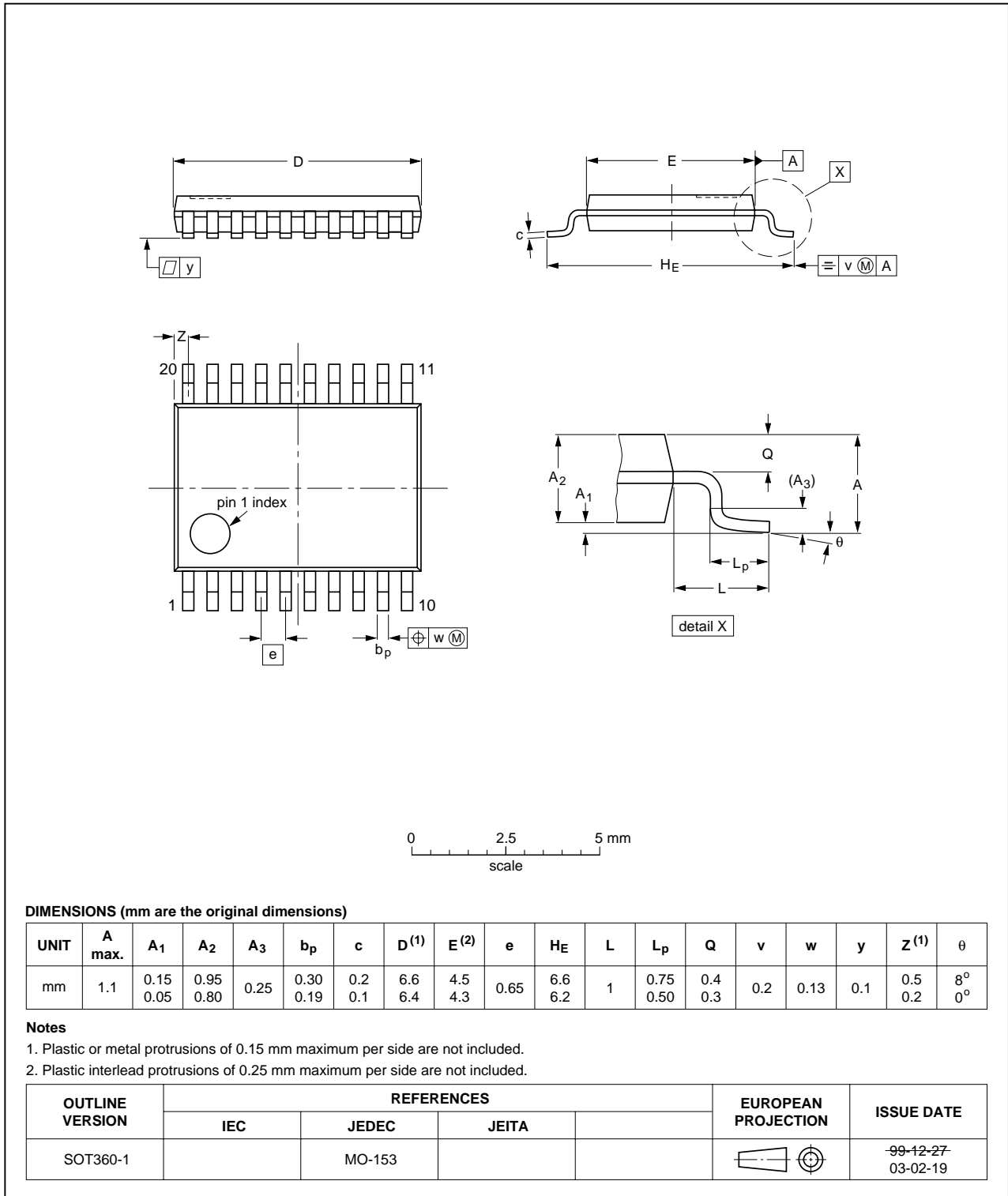


Fig 11. Package outline SOT360-1 (TSSOP20)

## 12. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

## 13. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT374_3	20080612	Product data sheet	-	74AHC_AHCT374_2
Modifications:	<ul style="list-style-type: none"> <li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>• Legal texts have been adapted to the new company name where appropriate.</li> <li>• <a href="#">Table 6</a>: the conditions for input leakage current have been changed.</li> </ul>			
74AHC_AHCT374_2	19990928	Product specification	-	74AHC_AHCT374_1
74AHC_AHCT374_1	19981211	Product specification	-	-

## 14. Legal information

### 14.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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